**PNP/NPN Epitaxial Planar Silicon Transistors** 



2SB1135/2SD1668

# **50V/7A Switching Applications**

## **Applications**

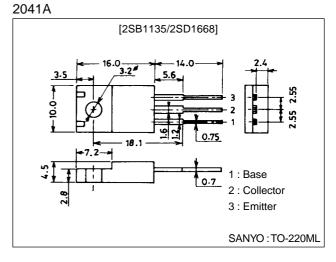
• Relay drivers, high-speed inverters, converters, and other general high-current switching applications.

### **Features**

- $\cdot$  Low-saturation collector-to-emitter voltage :
- V<sub>CE(sat)</sub>=-0.4V max.
- $\cdot$  Wide ASO leading to high resistance to breakdown.
- · Micaless package facilitating mounting.

# **Package Dimensions**

unit:mm



():2SB1135

# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		()6	V
Collector Current	ι <sub>C</sub>		(-)7	А
Collector Current (Pulse)	ICP		(–)12	A
Collector Dissipation	PC		2	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(–)0.1	mA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)0.1	mA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	70*		280*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)5A	30			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A		10		MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)4A, I <sub>B</sub> =(-)0.4A			(-)0.4	V

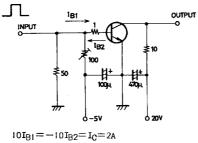
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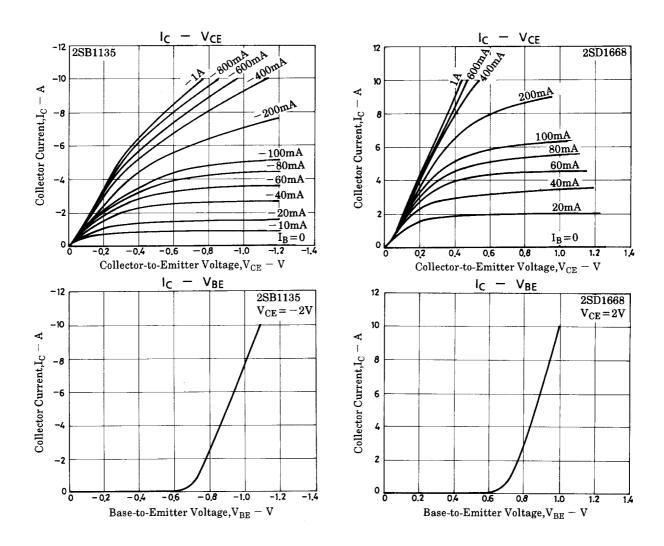
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)1mA, I <sub>E</sub> =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)1mA, I <sub>C</sub> =0	(–)6			V
Rise Time	ton	See specified Test Circuti.		0.2		μs
Storage Time	<sup>t</sup> stg	See specified Test Circuit.		(0.7)		μs
				0.9		μs
Fall Time	tf	See specified Test Circuit.		(0.1)		μs
				0.3		μs

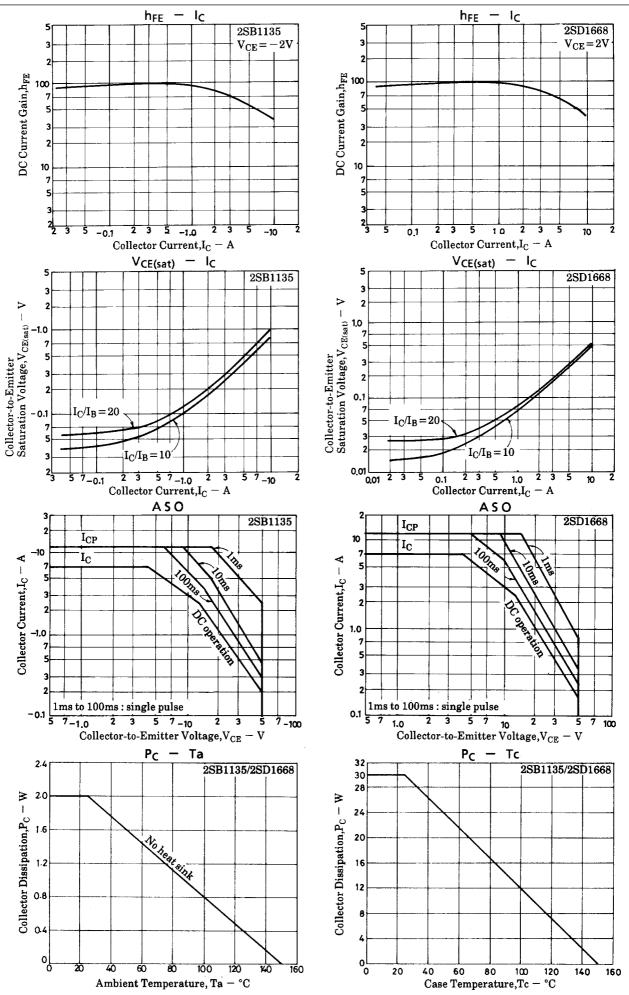
### **Switching Time Test Circuit**



For PNP, the polarity is reversed. Unit (resistance :  $\Omega$ , capacitance : F)



### 2SB1135/2SD1668



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